

MITSUBISHI Nch POWER MOSFET

# FS5KM-18A

HIGH-SPEED SWITCHING USE

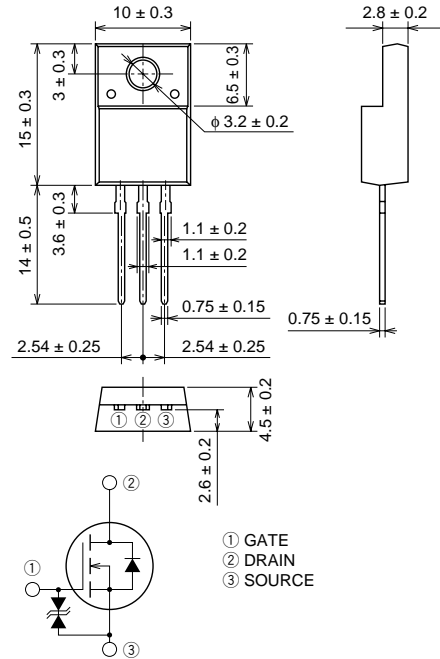
## FS5KM-18A



- V<sub>DSS</sub> ..... 900V
- r<sub>DS (ON)</sub> (MAX) ..... 2.8Ω
- I<sub>D</sub> ..... 5A
- V<sub>iso</sub> ..... 2000V

## OUTLINE DRAWING

Dimensions in mm



TO-220FN

## APPLICATION

SMPS, DC-DC Converter, battery charger, power supply of printer, copier, HDD, FDD, TV, VCR, personal computer etc.

## MAXIMUM RATINGS (T<sub>c</sub> = 25°C)

Symbol	Parameter	Conditions	Ratings	Unit
V <sub>DSS</sub>	Drain-source voltage	V <sub>GS</sub> = 0V	900	V
V <sub>GSS</sub>	Gate-source voltage	V <sub>DS</sub> = 0V	±30	V
I <sub>D</sub>	Drain current		5	A
I <sub>DM</sub>	Drain current (Pulsed)		15	A
P <sub>D</sub>	Maximum power dissipation		30	W
T <sub>ch</sub>	Channel temperature		-55 ~ +150	°C
T <sub>stg</sub>	Storage temperature		-55 ~ +150	°C
V <sub>iso</sub>	Isolation voltage	AC for 1minute, Terminal to case	2000	V <sub>rms</sub>
—	Weight	Typical value	2	g

Feb.1999



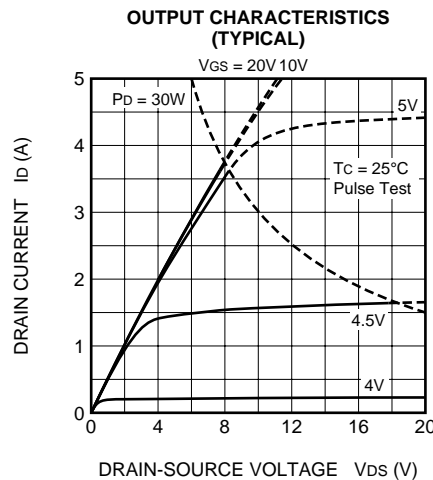
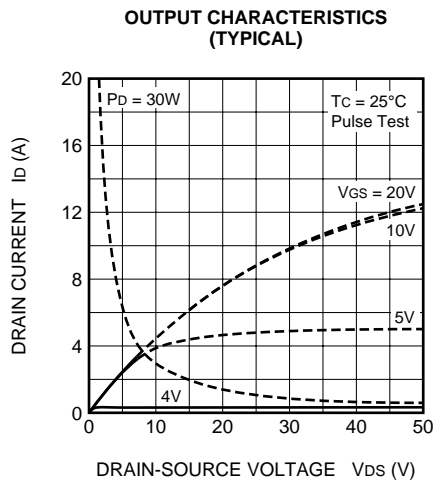
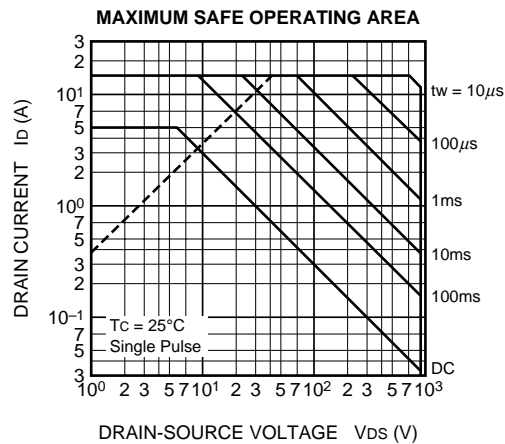
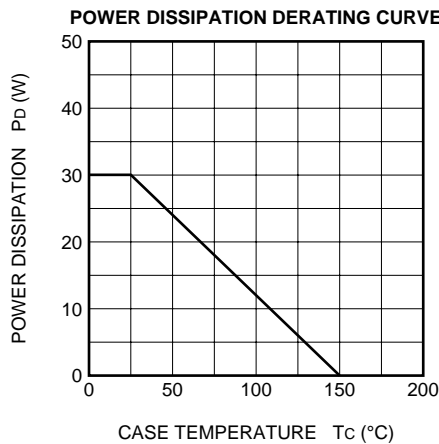
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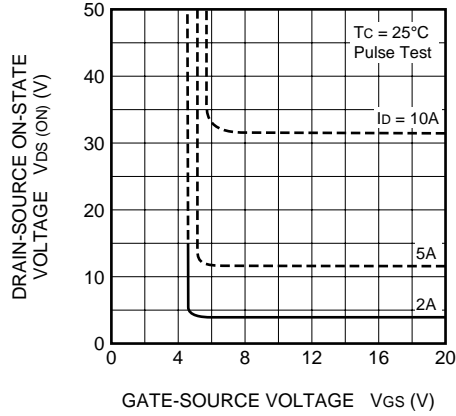
### ELECTRICAL CHARACTERISTICS (Tch = 25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V(BR)DSS	Drain-source breakdown voltage	Id = 1mA, VGS = 0V	900	—	—	V
V(BR)GSS	Gate-source breakdown voltage	IGS = ±100μA, VDS = 0V	±30	—	—	V
IGSS	Gate-source leakage current	VGS = ±25V, VDS = 0V	—	—	±10	μA
IDSS	Drain-source leakage current	VDS = 900V, VGS = 0V	—	—	1	mA
VGS(th)	Gate-source threshold voltage	Id = 1mA, VDS = 10V	2	3	4	V
rDS(ON)	Drain-source on-state resistance	Id = 2A, VGS = 10V	—	2.15	2.80	Ω
VDS(ON)	Drain-source on-state voltage	Id = 2A, VGS = 10V	—	4.30	5.60	V
yfs	Forward transfer admittance	Id = 2A, VDS = 10V	3.0	5.0	—	S
Ciss	Input capacitance	VDS = 25V, VGS = 0V, f = 1MHz	—	1050	—	pF
Coss	Output capacitance		—	100	—	pF
Crss	Reverse transfer capacitance		—	20	—	pF
td(on)	Turn-on delay time		—	20	—	ns
tr	Rise time	VDD = 200V, Id = 2A, VGS = 10V, RGEN = RGS = 50Ω	—	18	—	ns
td(off)	Turn-off delay time		—	110	—	ns
tf	Fall time		—	35	—	ns
VSD	Source-drain voltage	Is = 2A, VGS = 0V	—	1.0	1.5	V
Rth(ch-c)	Thermal resistance	Channel to case	—	—	4.17	°C/W

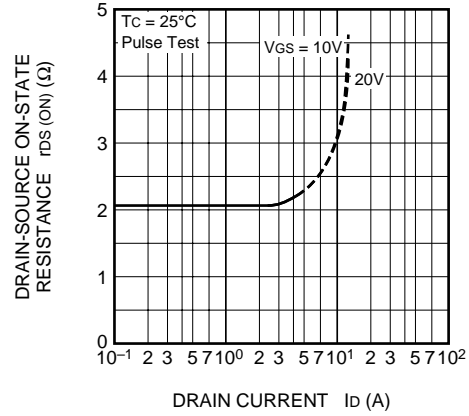
### PERFORMANCE CURVES



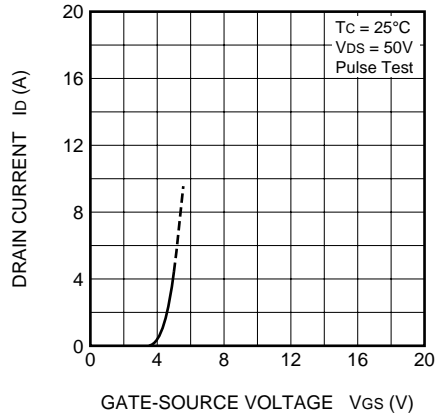
ON-STATE VOLTAGE VS. GATE-SOURCE VOLTAGE (TYPICAL)



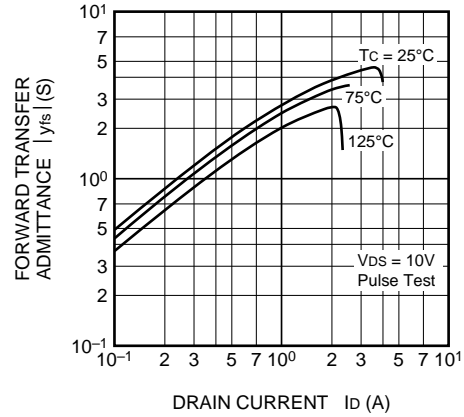
ON-STATE RESISTANCE VS. DRAIN CURRENT (TYPICAL)



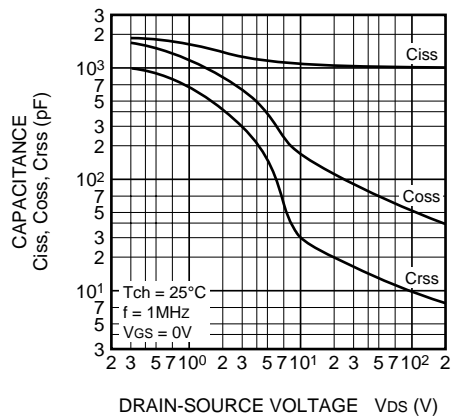
TRANSFER CHARACTERISTICS (TYPICAL)



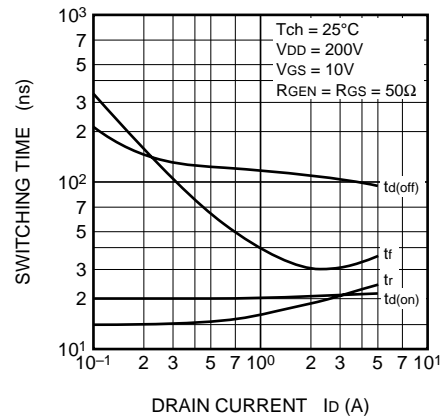
FORWARD TRANSFER ADMITTANCE VS. DRAIN CURRENT (TYPICAL)



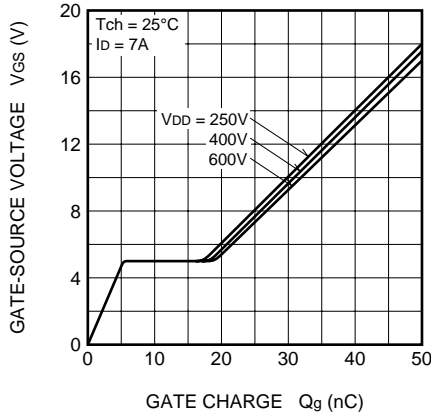
CAPACITANCE VS. DRAIN-SOURCE VOLTAGE (TYPICAL)



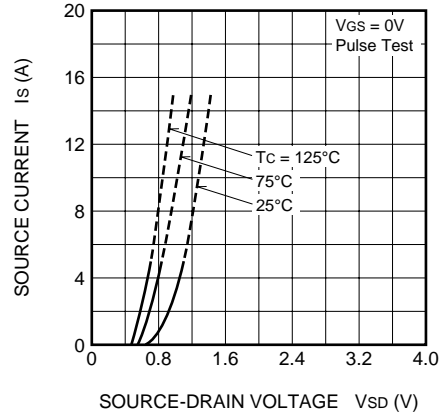
SWITCHING CHARACTERISTICS (TYPICAL)



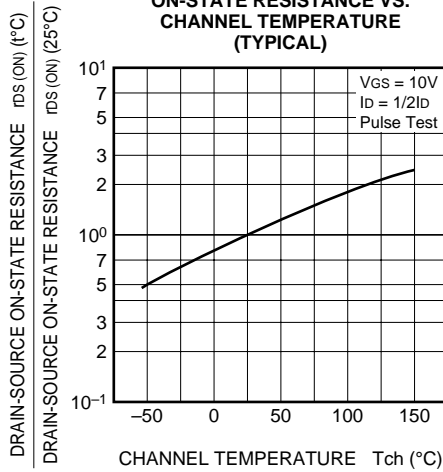
GATE-SOURCE VOLTAGE VS. GATE CHARGE (TYPICAL)



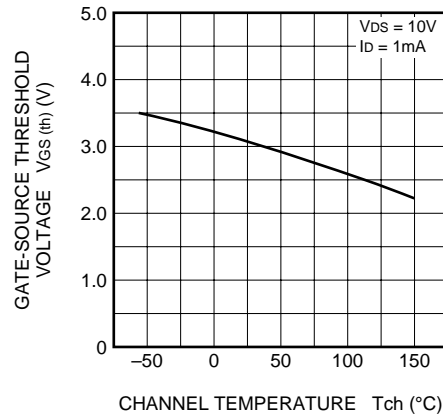
SOURCE-DRAIN DIODE FORWARD CHARACTERISTICS (TYPICAL)



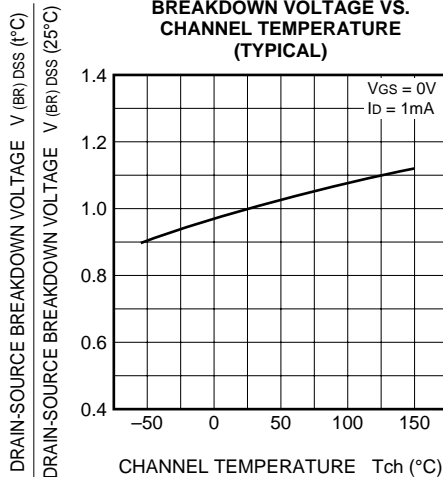
ON-STATE RESISTANCE VS. CHANNEL TEMPERATURE (TYPICAL)



THRESHOLD VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)



BREAKDOWN VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS

